WHAT IS CLAIMED IS:

1. A semiconductor laser device, comprising: a first conductivity type cladding layer; an active layer; and a second conductivity type cladding layer, which are on a substrate,

wherein the semiconductor laser device further comprises a stripe structure for injecting carriers therein,

a width of the stripe is wider at a front end face of a resonator from which laser light is emitted than at a rear end face that is located on an opposite side of the front end face, and

a reflectance of the front end face is lower than a reflectance of the rear end face.

2. The semiconductor laser device according to claim 1, wherein at least the active layer comprises a Group III–V nitride based semiconductor material.

3. The semiconductor laser device according to claim 2, wherein at least the active layer comprises an AlGaAs based semiconductor material.

4. The semiconductor laser device according to claim 2, wherein at least the active layer comprises an AlGaInP based semiconductor material.

5. The semiconductor laser device according to claim 1, wherein a ratio between the stripe width at the front end face and the stripe width at the rear end face satisfies a relationship of $1 <$ (the stripe width at the front end face) / (the stripe width at the rear end face) < 2.

6. The semiconductor laser device according to claim 5, wherein the ratio between the stripe width at the front end face and the stripe width at the rear end face satisfies a relationship of $1.4 <$ (the stripe width at the front end face) / (the stripe width at the rear end face) < 1.8.

7. The semiconductor laser device according to claim 1, wherein the width of the stripe decreases continuously from the front end face toward the rear end face.

8. The semiconductor laser device according to claim 1,

wherein the stripe structure has a region in which the width of the stripe varies continuously and a region in which the width of the stripe is constant, and

the stripe width at a boundary between the respective regions varies seamlessly.

9. The semiconductor laser device according to claim 1, wherein the stripe structure has regions adjacent to the front end face and the rear end face, the regions respectively extending inwardly from the front end face and the rear end face and each having a constant stripe width.

10. The semiconductor laser device according to claim 9, wherein the regions having the constant stripe widths extend inwardly from the front end face and the rear end face, respectively, by a length of one–twentieth or shorter of a length of the resonator.

11. The semiconductor laser device according to claim 1, wherein the reflectance of the front end face is lower than the reflectance of the rear end face by 15% or more.